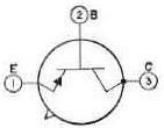
TRANSISTOR

2N2273

Germanium p-n-p type used for low-power radio-frequency amplifier applications in the vhf range in industrial and military equipment. JEDEC No. TO-18 package; outline 12, Outlines Section.



MAXIMUM RATINGS

Collector-to-Base Voltage (with emitter open)	−25 max	volts
Collector-to-Emitter Voltage (with base open)	−15 max	volts
Emitter-to-Base Voltage (with collector open)	−1 max	ma
Collector Current	−100 max	ma
Transistor Dissipation:		
At ambient temperatures up to 25°C	100 max	mw
At ambient temperatures above 25°C	See curve page 80	
Temperature Range:		
Operating (junction) and storage	−65 to 100	°C
Lead Temperature (for 10 seconds maximum)	235 max	°C

CHARACTERISTICS

Collector-to-Base Breakdown Voltage (with collector ma = 0.1 and emitter current = 0)	−25 min	volts
Collector-to-Emitter Breakdown Voltage (with collector ma = 0.1 and base current = 0)	−15 min	volts
Emitter-to-Base Breakdown Voltage (with emitter ma = 0.1 and collector current = 0)	−1 min	volt
Collector-Cutoff Current (with collector-to-base volts = −12 and emitter current = 0)	−10 max	μa

In Common-Base Circuit

Output Capacitance (with collector-to-base volts = −10, emitter current = 0, and frequency = 140 kilocycles)	3.5 max	pf

In Common-Emitter Circuit

DC Forward Current-Transfer Ratio (with collector-to-emitter volts = −10 and collector ma = −1)	20 to 150	
Small-Signal Forward Current-Transfer Ratio (with collector-to-emitter volts = −6, collector ma = −1, and frequency = 10 Mc)	20 to 28	
Base Spreading Resistance (with collector-to-emitter volts = −10, collector ma = −1, and frequency = 250 Mc)	250	ohms
High-Frequency Input Impedance (with collector-to-emitter volts = −9, collector ma = −1, and frequency = 250 Mc)	50 to 250	ohms
Small-Signal Power Gain (with collector-to-emitter volts = −9, collector ma = −1, and frequency = 30 Mc)	10 min	db